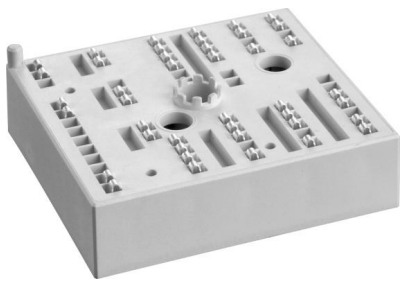


SKiiP 25NAB066V1



MiniSKiiP[®] 2

3-phase bridge rectifier +
brake chopper + 3-phase
bridge inverter
SKiiP 25NAB066V1

Target Data

Features

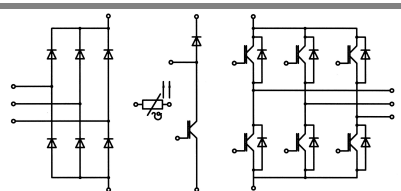
- Trench IGBTs
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised file no. E63532

Typical Applications

- Inverter up to 10 kVA
- Typical motor power 4,0 kW

Remarks

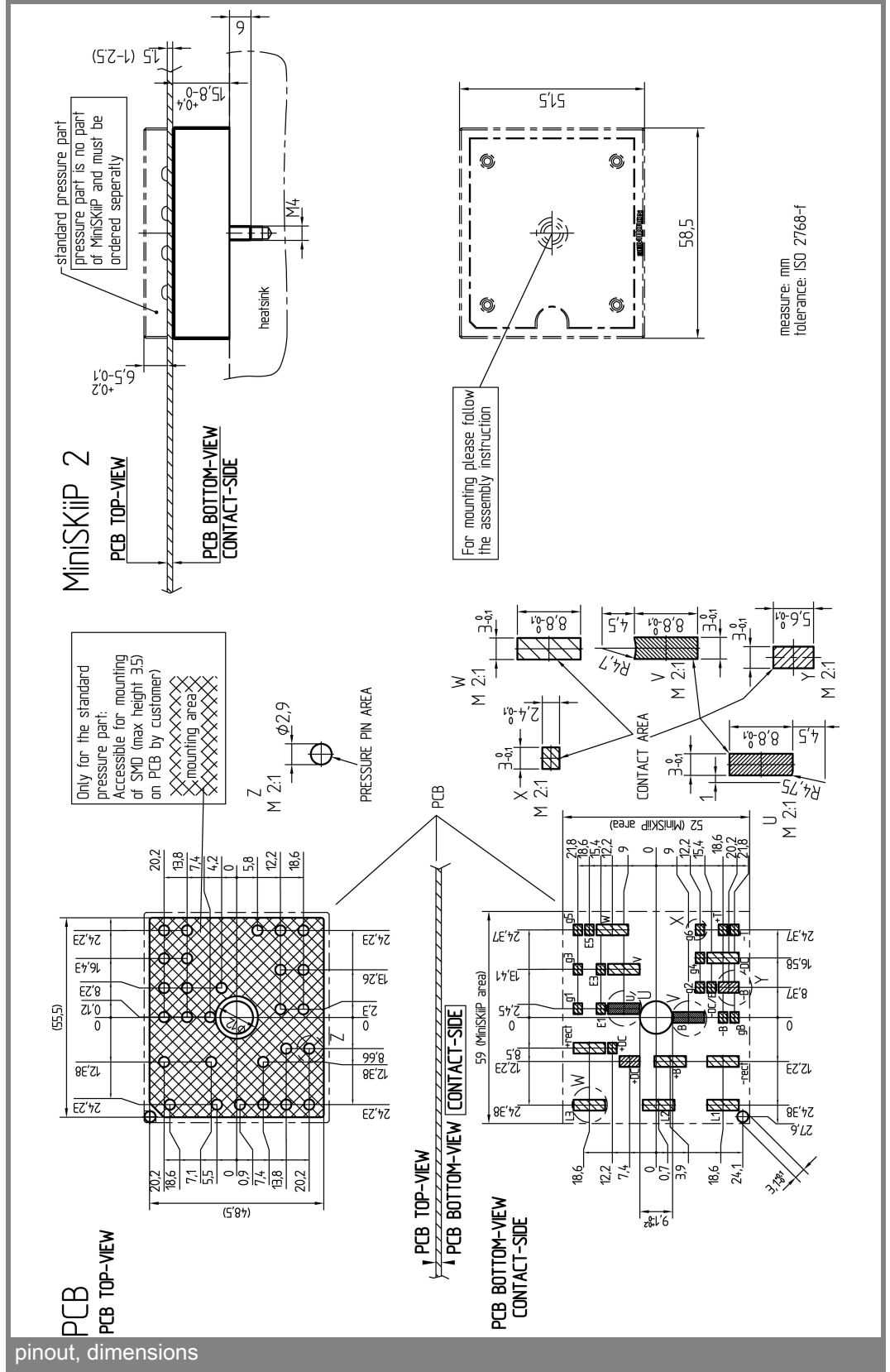
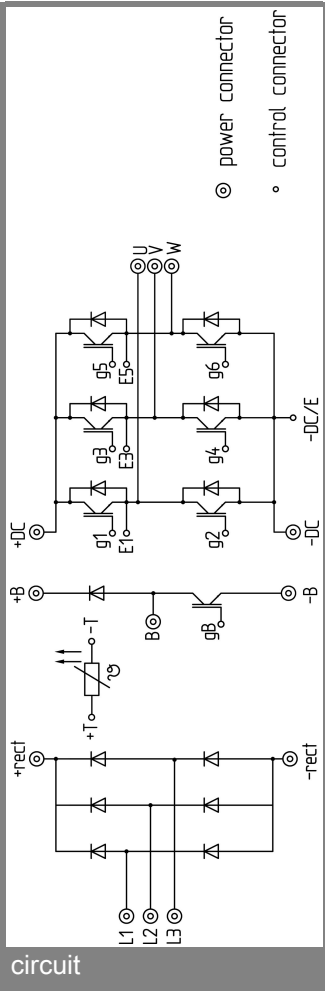
- Case temperature limited to $T_C = 125\text{ °C}$ max.



NAB

Absolute Maximum Ratings		$T_s = 25\text{ °C}$, unless otherwise specified	
Symbol	Conditions	Values	Units
IGBT - Inverter, Chopper			
V_{CES}		600	V
I_C	$T_s = 25\text{ (70) °C}$		A
I_{CRM}	$T_s = 25\text{ (70) °C}$, $t_p \leq 1\text{ ms}$		A
V_{GES}		± 20	V
T_j		- 40 ... + 175	°C
Diode - Inverter, Chopper			
I_F	$T_s = 25\text{ (70) °C}$		A
I_{FRM}	$T_s = 25\text{ (70) °C}$, $t_p \leq 1\text{ ms}$		A
T_j		- 40 ... + 175	°C
Diode - Rectifier			
V_{RRM}		800	V
I_F	$T_s = 70\text{ °C}$	46	A
I_{FSM}	$t_p = 10\text{ ms}$, $\sin 180\text{ °}$, $T_j = 25\text{ °C}$	370	A
i^2t	$t_p = 10\text{ ms}$, $\sin 180\text{ °}$, $T_j = 25\text{ °C}$	680	A ² s
T_j		- 40 ... + 150	°C
I_{tRMS}	per power terminal (20 A / spring)	60	A
T_{stg}	$T_{op} \leq T_{stg}$	- 40 ... + 125	°C
V_{isol}	AC, 1 min.	2500	V

Characteristics		$T_s = 25\text{ °C}$, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
IGBT - Inverter, Chopper					
V_{CEsat}	$I_C = 30\text{ A}$, $T_j = 25\text{ (125) °C}$	1,45 (1,65)	1,9 (2,05)		V
$V_{GE(th)}$	$V_{GE} = V_{CE}$, $I_C = 0,5\text{ mA}$	5,8			V
$V_{CE(TO)}$	$T_j = 25\text{ (125) °C}$	0,9 (0,85)	1 (0,9)		V
r_T	$T_j = 25\text{ (125) °C}$	27 (37)	40 (50)		mΩ
C_{ies}	$V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$, $f = 1\text{ MHz}$	-			nF
C_{oes}	$V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$, $f = 1\text{ MHz}$	-			nF
C_{res}	$V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$, $f = 1\text{ MHz}$	-			nF
$R_{th(j-s)}$	per IGBT	1,05			K/W
$t_{d(on)}$	under following conditions	-			ns
t_r	$V_{CC} = 300\text{ V}$, $V_{GE} = \pm 15\text{ V}$	-			ns
$t_{d(off)}$	$I_C = 30\text{ A}$, $T_j = 125\text{ °C}$	-			ns
t_f	$R_{Gon} = R_{Goff} = 20\text{ Ω}$	-			ns
E_{on}	inductive load	0,75			mJ
E_{off}		1,35			mJ
Diode - Inverter, Chopper					
$V_F = V_{EC}$	$I_F = 30\text{ A}$, $T_j = 25\text{ (125) °C}$	1,4	1,6		V
$V_{(TO)}$	$T_j = 25\text{ (125) °C}$	0,95	1		V
r_T	$T_j = 25\text{ (125) °C}$	15	20		mΩ
$R_{th(j-s)}$	per diode	1,5			K/W
I_{RRM}	under following conditions	-			A
Q_{rr}	$I_F = 30\text{ A}$, $V_R = 300\text{ V}$	-			μC
E_{rr}	$V_{GE} = 0\text{ V}$, $T_j = 125\text{ °C}$ $di_F/dt = -\text{ A}/\mu\text{s}$	-			mJ
Diode - Rectifier					
V_F	$I_F = 25\text{ A}$, $T_j = 25\text{ °C}$	1,1			V
$V_{(TO)}$	$T_j = 150\text{ °C}$	0,8			V
r_T	$T_j = 150\text{ °C}$	13			mΩ
$R_{th(j-s)}$	per diode	1,25			K/W
Temperature Sensor					
R_{ts}	3 %, $T_r = 25\text{ (100) °C}$	1000(1670)			Ω
Mechanical Data					
w		65			g
M_s	Mounting torque	2	2,5		Nm



This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.